



Mike Johnston, "Spaceman with Floating Pizza"

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Hands-on Wed.6

# Ionized-impurity and grain-boundary scatterings

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- Ionized-impurity scattering
- Grain-boundary scattering

# Theory for ionized-impurity scattering

- The development for this problem was published in [J. Leveillee, X. Zhang, E. Kioupakis, and F. Giustino, Phys. Rev. B **107**, 125207 (2023)].
- Infact, the real shape of the impurity potential depends the crystal structure, type of defect and its formation energy, which in principle requires sophisticated *ab initio* calculations for defect-containing supercells.
- The problem is simplified by considering the charged defects as point-charge system which is randomly distributed in host materials.

# Scattering by a single point-charged defect

- From [C. Verdi and F. Giustino, Phys. Rev. Lett. **115**, 176401 (2015)], the Coulomb potential generated by a periodic point charge  $Q$  in Born-von Kármán supercell at  $\tau$  is

$$\phi(\mathbf{r}; \tau) = \frac{4\pi}{\Omega} \frac{Q}{4\pi\epsilon_0} \frac{1}{N} \sum_{\mathbf{q}} \sum_{\mathbf{G} \neq -\mathbf{q}} \frac{e^{i(\mathbf{q}+\mathbf{G})(\mathbf{r}-\tau)}}{(\mathbf{q}+\mathbf{G})\epsilon(\mathbf{q}+\mathbf{G})}$$

- Considering an impurity with charge  $Q = \pm Ze$ , the potential energy feels by an electron at position  $\mathbf{r}$  is

$$V(\mathbf{r}; \tau) = \frac{-e^2}{4\pi\epsilon_0} \frac{4\pi Z}{\Omega_{\text{BvK}}} \sum_{\mathbf{q}} \sum_{\mathbf{G} \neq -\mathbf{q}} \frac{e^{i(\mathbf{q}+\mathbf{G})(\mathbf{r}-\tau)}}{(\mathbf{q}+\mathbf{G})\epsilon(\mathbf{q}+\mathbf{G})}$$

- The ionized-impurity scattering matrix between two states  $|n\mathbf{k}\rangle$  and  $|m\mathbf{k} + \mathbf{q}\rangle$

$$g_{mn}^{\text{imp}}(\mathbf{k}, \mathbf{q}; \tau) = \frac{-e^2}{4\pi\epsilon_0} \frac{4\pi Z}{\Omega_{\text{BvK}}} \sum_{\mathbf{G} \neq -\mathbf{q}} \frac{e^{i(\mathbf{q}+\mathbf{G})\tau} \langle u_{m\mathbf{k}+\mathbf{q}} | e^{i\mathbf{G}\mathbf{r}} | u_{n\mathbf{k}} \rangle_{\text{uc}}}{(\mathbf{q}+\mathbf{G})\epsilon(\mathbf{q}+\mathbf{G})}$$

# Scattering by multiple point-charged defects

- We consider a set of  $N_{\text{imp}}$  impurities at position  $\tau_1, \tau_2, \dots, \tau_{N_{\text{imp}}}$ , the scattering matrix

$$g_{mn}^{\text{imp}}(\mathbf{k}, \mathbf{q}; \{\tau\}) = \frac{-e^2}{4\pi\epsilon_0} \frac{4\pi Z}{\Omega_{\text{BvK}}} \sum_{\mathbf{G} \neq -\mathbf{q}} \frac{\langle u_{m\mathbf{k}+\mathbf{q}} | e^{i\mathbf{G}\mathbf{r}} | u_{n\mathbf{k}} \rangle_{\text{uc}}}{(\mathbf{q}+\mathbf{G})\epsilon(\mathbf{q}+\mathbf{G})} \sum_{I=1}^{N_{\text{imp}}} e^{-i(\mathbf{q}+\mathbf{G})\tau_I}$$

- The total scattering rate of state  $|n\mathbf{k}\rangle$  in Born's approximation is

$$\frac{1}{\tau_{n\mathbf{k}}^{\text{imp}}} = \sum_{m\mathbf{q}} \frac{2\pi}{\hbar} |g_{mn}^{\text{imp}}(\mathbf{k}, \mathbf{q}; \{\tau\})|^2 \delta(\epsilon_{n\mathbf{k}} - \epsilon_{m\mathbf{k}+\mathbf{q}}) = \sum_{m\mathbf{q}} \Gamma_{n\mathbf{k} \rightarrow m\mathbf{k}+\mathbf{q}}^{\text{imp}}$$

- Kohn-Luttinger ensemble average of scattering rate gives

$$\Gamma_{n\mathbf{k} \rightarrow m\mathbf{k}+\mathbf{q}}^{\text{imp,ave}} = n_{\text{ii}} \frac{2\pi}{\hbar} \left[ \frac{e^2}{4\pi\epsilon_0} \frac{4\pi Z}{\Omega} \right]^2 \sum_{\mathbf{G} \neq -\mathbf{q}} \frac{|\langle u_{m\mathbf{k}+\mathbf{q}} | e^{i\mathbf{G}\mathbf{r}} | u_{n\mathbf{k}} \rangle_{\text{uc}}|^2}{|(\mathbf{q}+\mathbf{G})\epsilon(\mathbf{q}+\mathbf{G})|^2} \delta(\epsilon_{n\mathbf{k}} - \epsilon_{m\mathbf{k}+\mathbf{q}})$$

# Scattering by grain-boundary

- Grain-boundary scattering can be calculated using the simplest possible model, whereby the relaxation time is given by

$$\tau_{n\mathbf{k}}^{\text{gb}} = L/|\mathbf{v}_{n\mathbf{k}}|,$$

where,  $L$  is grain size and  $\mathbf{v}_{n\mathbf{k}}$  is group velocity of carrier.

- **Exercise 1** and **Exercise 2** will show you how ionized-impurity and grain-boundary scatterings impact on carrier mobility, respectively. The system is chosen for this tutorial is cubic BN (c-BN), the same as in “Exercise 1 of Hands-on Wed.5”

- J. Leveillee, X. Zhang, E. Kioupakis, and F. Giustino, Phys. Rev. B **107**, 125207 (2023) [[link](#)]
- C. Verdi and F. Giustino, Phys. Rev. Lett. **115**, 176401 (2015) [[link](#)]
- N. Mingo and D. A. Broido, Nano Lett. **5**, 1221 (2005) [[link](#)]